

L Number	Hits	Search Text	DB	Time stamp
19	2650	257/295	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
20	634	257/305	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
21	1643	257/310	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
22	841	257/345	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
23	816	257/349	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
24	1011	257/632	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
25	760	257/640	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
26	7308	257/295 257/305 257/310 257/345 257/349 257/632 257/640	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
27	268	(257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:49
28	327	(257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:50
29	474	((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:50
30	392	((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (oxygen or oxidation or oxidizing))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:50
31	34	((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (oxygen or oxidation or oxidizing)) and ("n.sub.2 h.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:50

32	15	(((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (oxygen or oxidation or oxidizing)) and ("h.sub.2 n.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:50
33	39	(((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (oxygen or oxidation or oxidizing)) and ("n.sub.2 h.sub.2")) (((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (oxygen or oxidation or oxidizing)) and ("h.sub.2 n.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 18:53
34	974	(257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (prevent\$ with (oxygen or oxidiz\$ or oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:13
35	2	("6303972").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:27
36	10	(257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:36
37	5509	substrate and (conductor or electrode) and (phosphine or methylsilane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:36
38	3342	257/\$ and (conductor or electrode) and (phosphine or methylsilane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:37
39	125	(257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (conductor or electrode) and (phosphine or methylsilane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:39
40	4228	(257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (oxygen or oxidation or oxidizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:39
41	49401	((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (oxygen or oxidation or oxidizing)) and (conductor or electrode) or (phosphine or methylsilane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:40
42	117	((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (oxygen or oxidation or oxidizing)) and (conductor or electrode) and (phosphine or methylsilane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:41
43	18	((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (conductor or electrode) and (phosphine or methylsilane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:49

44	18	(((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (conductor or electrode) and (phosphine or methylsilane)) and (oxygen or oxidation or oxidizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:42
45	28	(((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (phosphine or methylsilane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:49
46	10	(((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (phosphine or methylsilane)) not (((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and (conductor or electrode) and (phosphine or methylsilane))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:50
47	10	(((((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and wn) ((257/295 257/305 257/310 257/345 257/349 257/632 257/640) and (tungsten adj nitride))) and methylsilane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/24 19:50